
HSM2692

Silicon Epitaxial Planar Diode for Tuner Band Switch

HITACHI

ADE-208-093A (Z)

Preliminary

Rev. 1

Jun. 1993

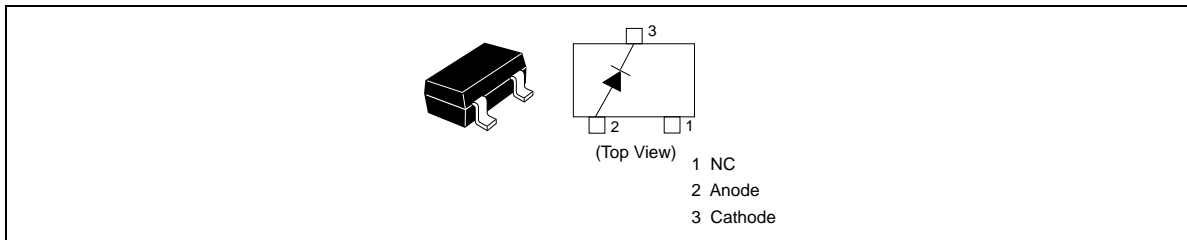
Features

- Low forward resistance. ($r_f = 0.9\Omega_{\text{max}}$)
- Low capacitance. ($C = 1.2\text{pF}_{\text{max}}$)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM2692	B1	MPAK

Pin Arrangement



HSM2692

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-45 to +125	°C
Operation temperature	T_{opr}	-20 to +60	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	35	—	—	V	$I_R = 10\mu A$
Reverse current	I_R	—	—	50	nA	$V_R = 25V$
Forward voltage	V_F	—	—	1.0	V	$I_F = 10mA$
Capacitance	C	—	—	1.2	pF	$V_R = 6V, f = 1MHz$
Forward resistance	r_f	—	—	0.9	Ω	$I_F = 2mA, f = 100MHz$

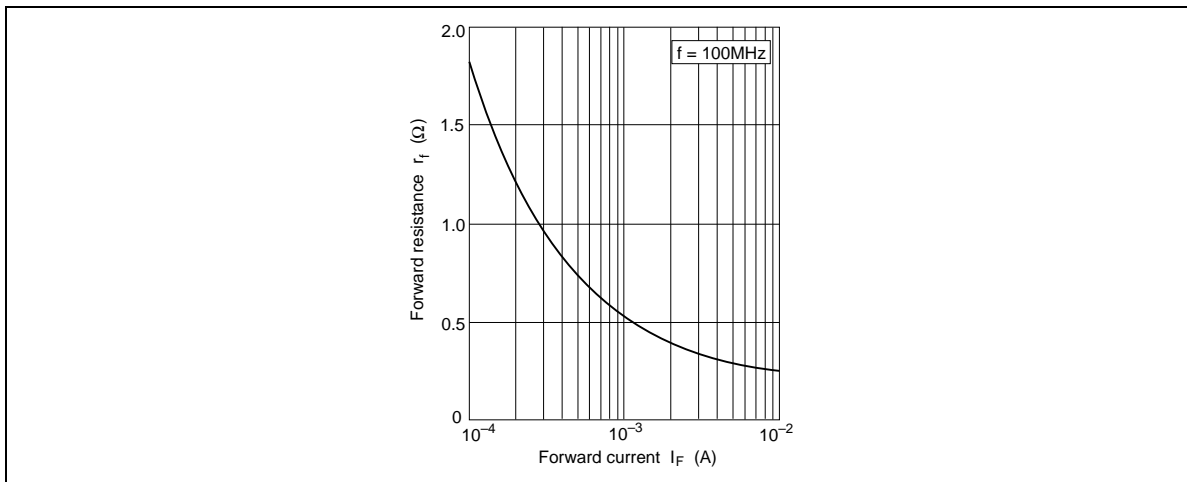


Fig.1 Forward resistance Vs. Forward current

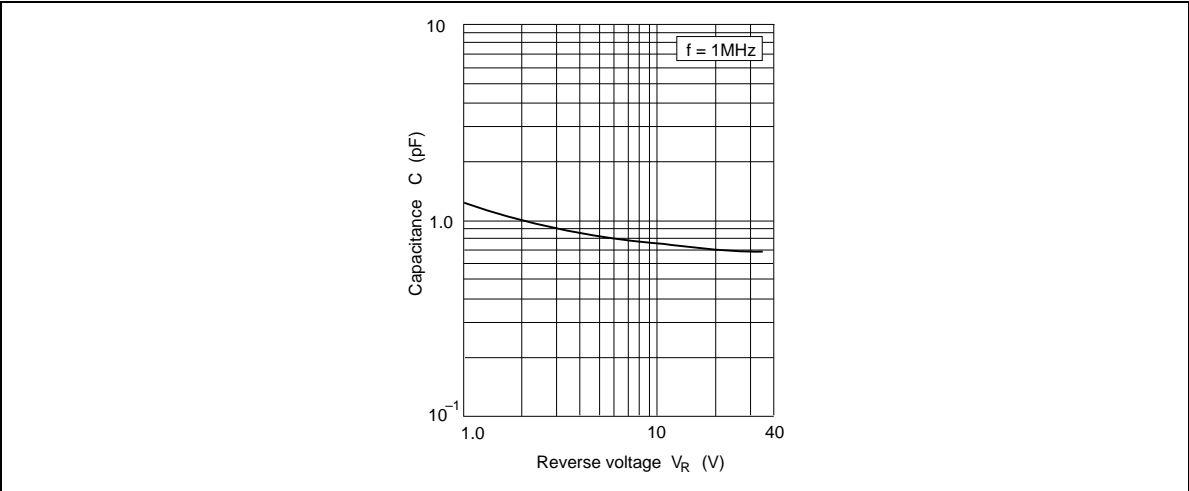


Fig.2 Capacitance Vs. Reverse voltage

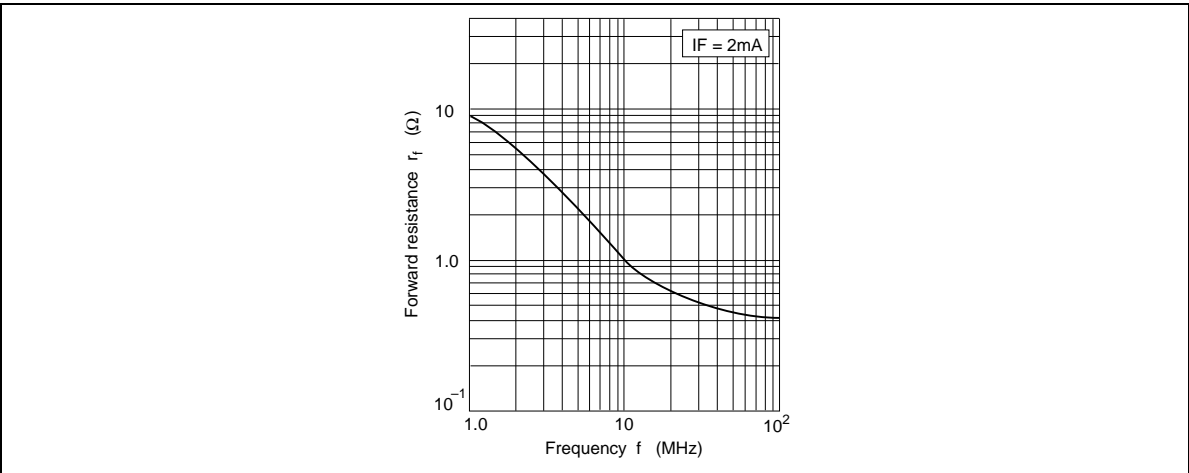


Fig.3 Forward resistance Vs. Frequency

HSM2692

Package Dimensions

